Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Trench MOSFET technology
- Ultra low Q_G and Q_{GD} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- MLPAK33 package (3.3 x 3.3 mm footprint)

3. Applications

- DC to DC conversion
- · Battery management
- · Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	12	Α
Static characte	eristics						
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I_D = 7.9 A; T_j = 25 °C		-	14.8	17.4	mΩ
resistance	V_{GS} = 4.5 V; I_D = 6.8 A; T_j = 25 °C		-	18.5	23.1	mΩ	
Dynamic chara	cteristics						
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_{D} = 6.8 A; V_{GS} = 4.5 V; I_{j} = 25 °C		-	2.5	3.8	nC

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	D
2	S	source		
3	S	source		G (F)
4	G	gate	l h d	mbb076 S
5	D	drain		
6	D	drain		
7	D	drain	MLPAK33 (SOT8002-1)	
8	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package	Package							
	Name	Description	Version						
PXN017-30QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1						

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN017-30QL	9АВ

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	12	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	7.9	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	5	Α
		V _{GS} = 10 V; T _{sp} = 25 °C		-	20	Α
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	163	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T _{amb} = 25 °C	[1]	-	1.7	W
		T _{sp} = 25 °C		-	10.9	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode				•	
Is	source current	T _{amb} = 25 °C	[1]	-	1.6	Α
Avalanche rug	gedness		,	'		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 1 A; DUT in avalanche (unclamped)		-	15	mJ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

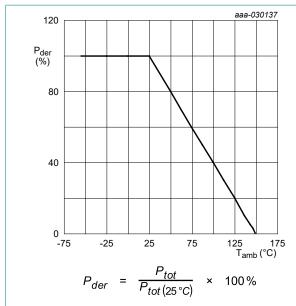


Fig. 1. Normalized total power dissipation as a function of ambient temperature

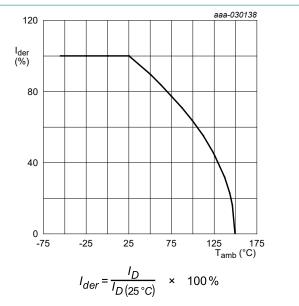


Fig. 2. Normalized continous drain current as a function of ambient temperature

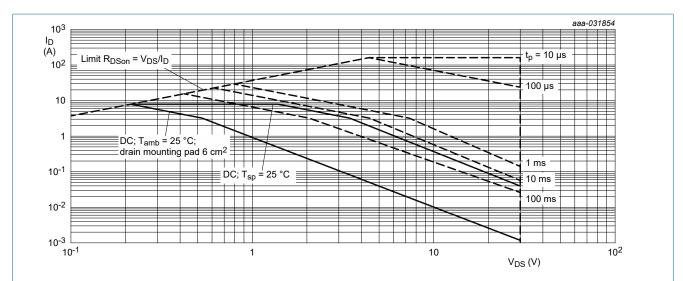


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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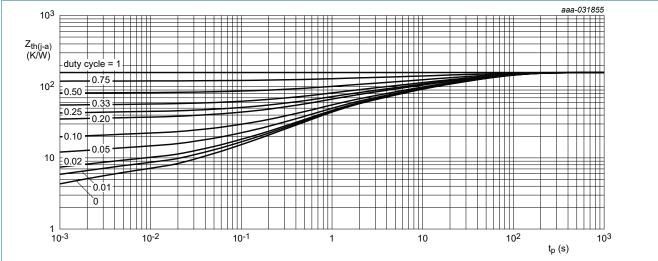
30 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

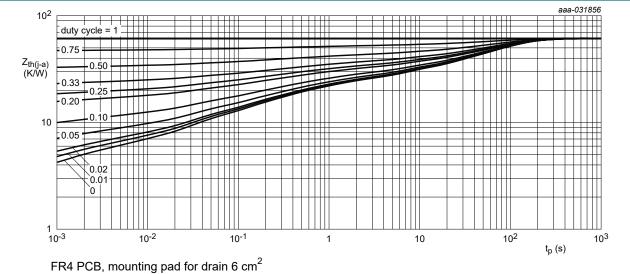
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance from	<u> </u>	[1]	-	160	200	K/W
	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	28	33	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	8.3	11.5	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.7	2.2	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 7.9 \text{ A}; T_j = 25 \text{ °C}$	-	14.8	17.4	mΩ
resistance	resistance	$V_{GS} = 10 \text{ V}; I_D = 7.9 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	22.9	27	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 6.8 \text{ A}; T_j = 25 \text{ °C}$	-	18.5	23.1	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7.9 \text{ A}; T_j = 25 \text{ °C}$	-	15	-	S
R _G	gate resistance	f = 1 MHz	-	3	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_{D} = 7.9 A; V_{GS} = 10 V; T_{j} = 25 °C	-	5.1	7.7	nC
		$V_{DS} = 15 \text{ V}; I_D = 6.8 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	2.5	3.8	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.9	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	0.5	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	0.4	-	nC
Q _{GD}	gate-drain charge		-	0.7	-	nC
V_{GSpl}	gate-source plateau voltage	V _{DS} = 15 V; I _D = 6.8 A; T _j = 25 °C	-	2.5	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	350	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	186	-	pF
C _{rss}	reverse transfer capacitance	-	-	21	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 6.8 A; V _{GS} = 4.5 V;	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	8	-	ns
t _{d(off)}	turn-off delay time	- 	-	6	-	ns
t _f	fall time		-	3	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 1.6 A; V _{GS} = 0 V; T _j = 25 °C	-	0.7	1.2	V
t _{rr}	reverse recovery time	I _S = 1.6 A; dI _S /dt = -100 A/μs;	-	15	-	ns
Q _r	recovered charge	V _{GS} = 4.5 V; V _{DS} = 15 V; T _j = 25 °C	-	6	-	nC
t _a	reverse recovery rise time		-	8	-	ns
t _b	reverse recovery fall time		-	7	-	ns

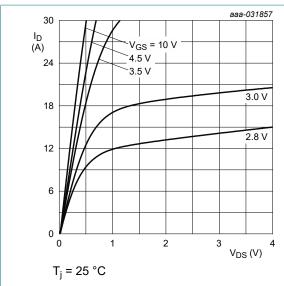


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

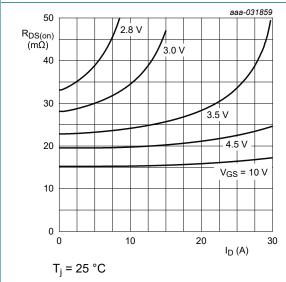


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

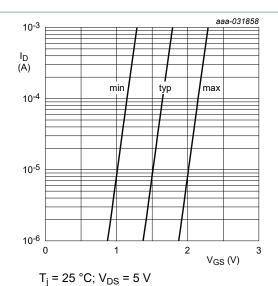


Fig. 7. Subthreshold drain current as a function of gate-source voltage

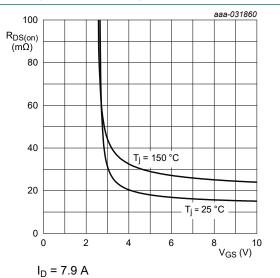


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

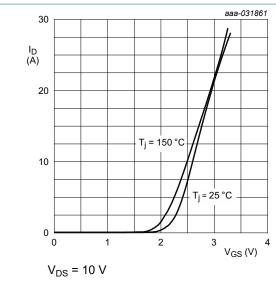


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

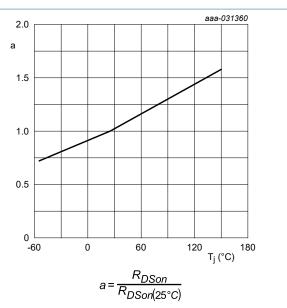


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

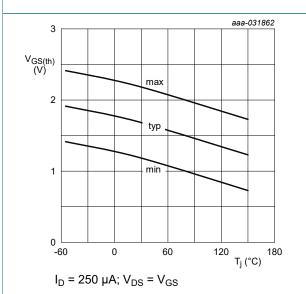


Fig. 12. Gate-source threshold voltage as a function of junction temperature

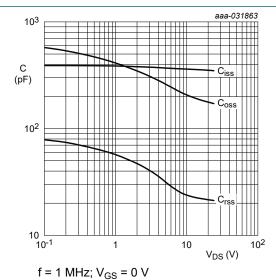


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

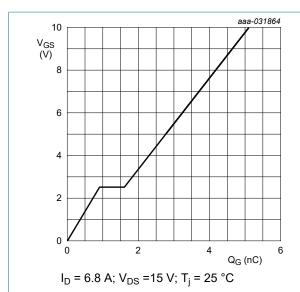


Fig. 14. Gate-source voltage as a function of gate charge; typical values

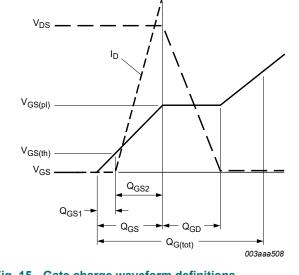


Fig. 15. Gate charge waveform definitions

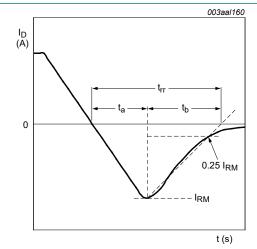


Fig. 16. Reverse recovery timing definition

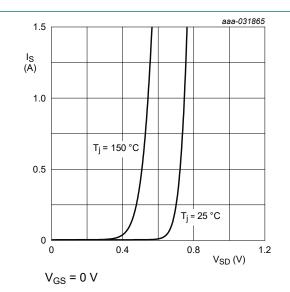
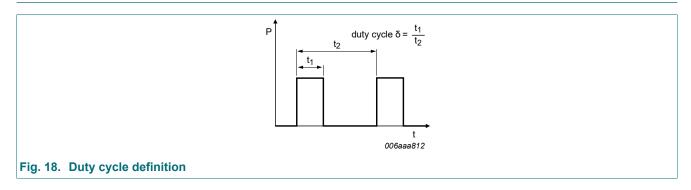


Fig. 17. Source current as a function of source-drain voltage; typical values

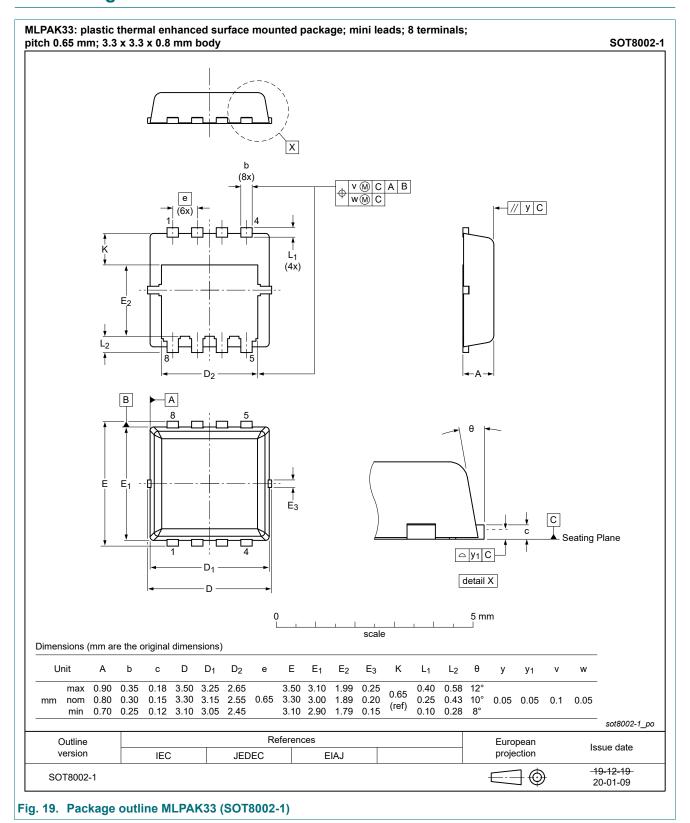
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11. Test information



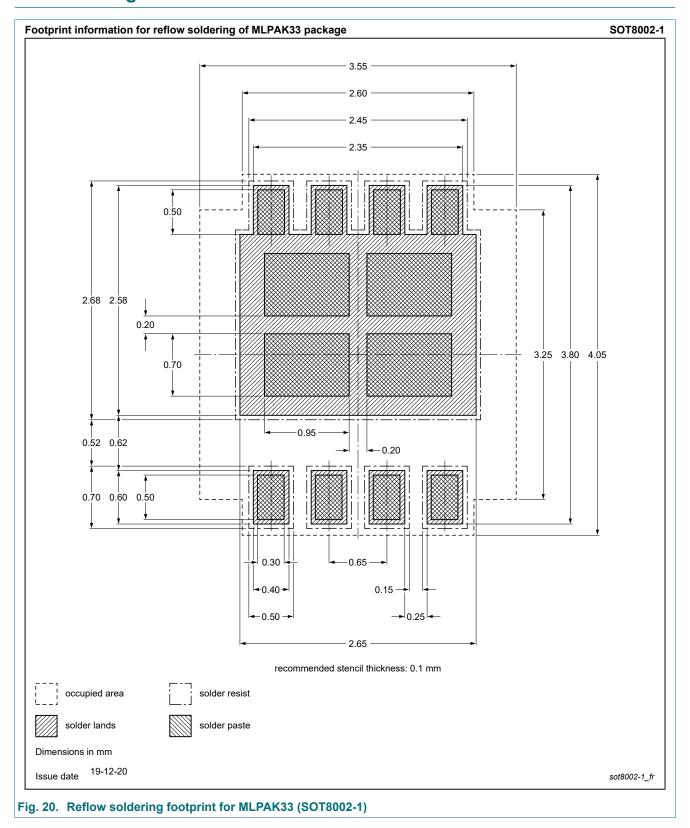
30 V, N-channel Trench MOSFET

12. Package outline



30 V, N-channel Trench MOSFET

13. Soldering



30 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXN017-30QL v.1	20201102	Product data sheet	-	-

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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